

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

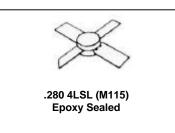
PHONE: (215) 631-9840 FAX: (215) 631-9855

MS2206

RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

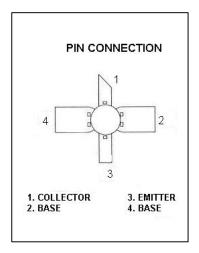
Features

- 1025-1150 MHz
- GOLD METALLIZATION
- INFINITE VSWR CAPABILITY @ RATED CONDITIONS
- Pout = 4 W MINIMUM
- G_P= 10 dB
- COMMON BASE CONFIGURATION



DESCRIPTION:

The MS2206 is a common base, silicon NPN microwave transistor designed for Class C driver applications under DME or IFF pulse conditions. This device is capable of withstanding an infinite load VSWR at any phase angle under rated conditions.



ABSOLUTE MAXIMUM RATINGS (Tcase = 25° C)

Symbol	Parameter	Value	Unit
P _{DISS}	Power Dissipation	7.5	W
V _{CE}	Collector-Emitter Bias Voltage	37	V
TJ	Junction Temperature	200	°C
Ic	Device Current	1.0	Α
T _{STG}	Storage Temperature	-65 to +200	٥С

Thermal Data

R _{TH(J-C)}	Junction-case Thermal Resistance*	35	°C/W





ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol	Test Conditions		Value			Unit	
Syllibol	rest conditions		Mi	า. Ty	p.	Max.	Offit
BV _{CBO}	I _C = 1 mA	I _E = 0 mA	45	; <u> </u>	-		V
BV _{CEO}	$I_C = 5 \text{ mA}$	I _B = 0mA	20		-		V
BV _{EBO}	I _E = 1.0 mA	$I_C = 0 \text{ mA}$	3.9	5 -	-		V
I _{CES}	V _{CE} = 35 V			·	-	1.0	mA
HFE	V _{CE} = 5 V	I _C = 100 mA	20		-	120	

DYNAMIC

Symbol	Test Conditions	Value			Unit
Symbol Test Conditions			Typ.	Max.	
P _{out}	f =1025 - 1150 MHz P _{IN} = 400mW V _{CE} =35V	4			W
G₽	f =1025 - 1150 MHz P _{IN} = 400mW V _{CE} =35V	10			dB

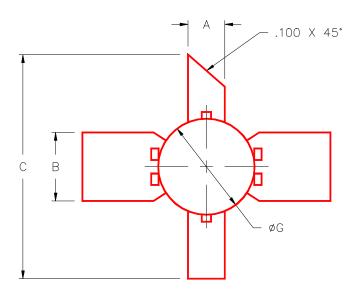
Conditions: Pulse Width = 10 μ s Duty Cycle = 1%





PACKAGE MECHANICAL DATA

PACKAGE STYLE M115





	MINIMUM	MAXIMUM	MINIMUM	MAXIMUM
	INCHES/MM	INCHES/MM	INCHES/MM	INCHES/MM
Α	.095/2,41	.105/2,67		
В	.195/4,95	.205/5,21		
С	1.000/25,40			
D	.004/0,10	.007/0,18		
Е	.050/1,27	.065/1,65		
F	.120/3,05	.135/3,43		
G	.275/6,99	.285/7,21		